EXPRESS MAIL MAILING LABEL

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INFORMATION DISCLOSURE STATEMENT	APPLICANT: Fitzgerald
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
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	A192	5,571,373	11/05/1996	Krishna et al.			
	A193	5,633,202	05/27/1997	Brigham et al.			
	A194	5,710,450	01/20/1998	Chau et al.			
	A195	5,976,939	11/02/1999	Thompson et al.			
	A196	6,876,053	04/05/2005	Ma et al.			

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	C137	Cao et al., "0.18-μm Fully-Depleted Silicon-on -Insulator MOSFET's," IEEE Electron Device Letters, 18(6):251-253 (1997).
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	C170	O'Neill, et al., "Deep Submicron CMOS Based on Silicon Germanium Technology," *Fellow*, IEEE Transactions on Electron Devices, Vol. 43, No. 6, June 1996 pp. 911-918.
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